



Energy states in GaAs delta-doped field effect transistors under hydrostatic pressure

J.C. Martínez-Orozco ^a✉, I. Rodríguez-Vargas ^b, M.E. Mora-Ramos ^a, C.A. Duque ^c

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Abstract

The study of the electronic structure in GaAs-based delta-doped field effect transistors under applied hydrostatic pressure is presented. A combination of the depletion approximation and the local density Thomas-Fermi theory is